



*A. Chrusa*  
10/31/02  
**PATENT**  
OCT 25 2002  
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TECHNOLOGY CENTER 2800

Docket No.: 49657-986

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of

Takao KAMOSHIMA, et al.

Serial No.: 09/779,565

Group Art Unit: 2814

Filed: February 09, 2001

Examiner: T. Le

For: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

**AMENDMENT**

Commissioner for Patents  
Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in response to the Office  
Action dated July 26, 2002.

**IN THE SPECIFICATION:**

✓ Please delete the title [SEMICONDUCTOR DEVICE AND  
MANUFACTURING METHOD THEREOF] and insert the following new title:

SEMICONDUCTOR DEVICE

*sub  
C1*

✓ Page 9, please amend the paragraph beginning at line 1 as follows.

Titanium nitride film 3 has a thickness of about 100 nm. A thickness of low-  
temperature aluminum film 4 including polycrystalline aluminum is about 150 nm and  
has an average crystal grain size of about 0.5µm. High-temperature aluminum film 5 is